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## **TSHF5210**

RoHS

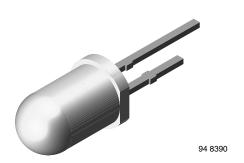
HALOGEN

FREE

GREEN (5-2008)

Vishay Semiconductors

# High Speed Infrared Emitting Diode, 890 nm, **Surface Emitter Technology**



#### **DESCRIPTION**

TSHF5210 is an infrared, 890 nm emitting diode based on surface emitter chip technology with high radiant power and high speed, molded in a clear, untinted plastic package.

#### **FEATURES**

· Package type: leaded Package form: T-1¾

• Dimensions (in mm): Ø 5

Leads with stand-off

Peak wavelength: λ<sub>p</sub> = 890 nm

High reliability

High radiant power

High radiant intensity

• Angle of half intensity:  $\varphi = \pm 8^{\circ}$ 

· Low forward voltage

Suitable for high pulse current operation

Good spectral matching with Si photodetectors

· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



- · Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- · Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK coded, 450 kHz or 1.3 MHz)

PRODUCT SUMMARY					
COMPONENT	I <sub>e</sub> (mW/sr)	φ <b>(°)</b>	$\lambda_{\mathbf{p}}$ (nm)	t <sub>r</sub> (ns)	
TSHF5210	327	± 8	890	10	

#### Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TSHF5210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾		

#### Note

· MOQ: minimum order quantity

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V <sub>R</sub>	5	V
Forward current		I <sub>F</sub>	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I <sub>FM</sub>	200	mA
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1	А
Power dissipation		P <sub>V</sub>	170	mW
Junction temperature		Tj	100	°C
Ambient temperature range		T <sub>amb</sub>	-40 to +85	°C
Storage temperature range		T <sub>stg</sub>	-40 to +100	°C
Soldering temperature	t ≤ 5 s, 2 mm from case	T <sub>sd</sub>	260	°C
Thermal resistance junction to ambient	J-STD-051, leads 7 mm, soldered on PCB	R <sub>thJA</sub>	230	K/W





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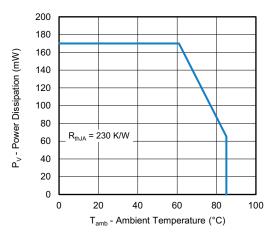


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

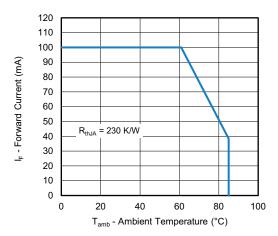


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V <sub>F</sub>	-	1.5	1.7	V
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	V <sub>F</sub>	-	3	-	V
Temperature coefficient of V <sub>F</sub>	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	TK <sub>VF</sub>	-	-1.3	-	mV/K
Reverse current		I <sub>R</sub>	Not designed for reverse operation			μΑ
Junction capacitance	$V_R = 0 \text{ V, f} = 1 \text{ MHz, E} = 0 \text{ mW/cm}^2$	C <sub>j</sub>	-	55	-	pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l <sub>e</sub>	150	327	450	mW/sr
	$I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$	l <sub>e</sub>	-	2700	-	mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	φ <sub>e</sub>	-	53	-	mW
Temperature coefficient of $\phi_e$	I <sub>F</sub> = 100 mA	TKφe	-	-0.3	-	%/K
Angle of half intensity		φ	-	± 8	-	٥
Peak wavelength	I <sub>F</sub> = 100 mA	$\lambda_{p}$	-	890	-	nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ	-	40	-	nm
Temperature coefficient of $\lambda_p$	I <sub>F</sub> = 100 mA	$TK\lambda_p$	-	0.3	-	nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>	-	10	-	ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>	-	10	-	ns

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I<sub>=</sub> = 100 mA

 $t_{\rm D}^{\cdot}$  = 20 ms

## BASIC CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

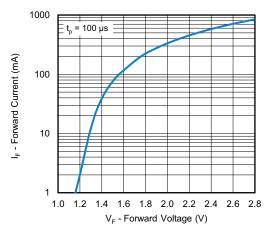
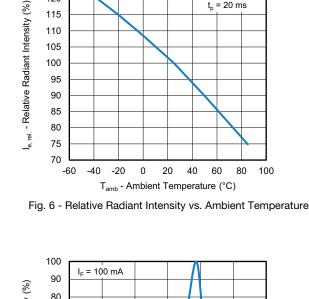


Fig. 3 - Forward Current vs. Forward Voltage



125

120

115

110

105

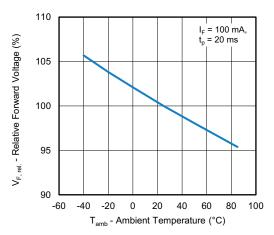
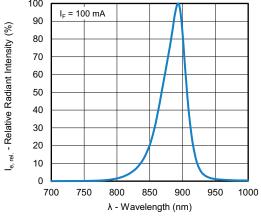


Fig. 4 - Relative Forward Voltage vs Ambient Temperature



20 40 60 80 100

0

Fig. 7 - Relative Radiant Intensity vs. Wavelength

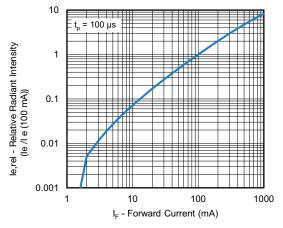


Fig. 5 - Relative Radiant Intensity vs. Forward Current

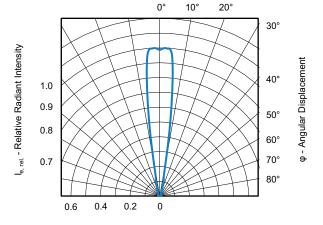


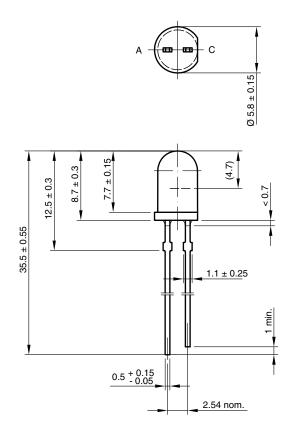
Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

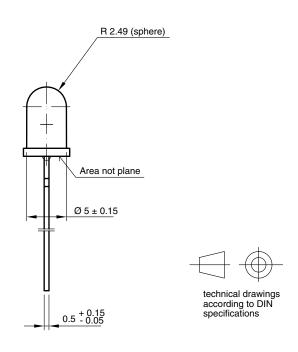


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### **PACKAGE DIMENSIONS** in millimeters





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